

**Amendments to the Specification:**

Please replace the paragraph [0025] with the following amended paragraph:

**[0025]** In the course of dry-etching the Al layer 210b, plasma ions (A, B, C) for etching go on in various ways: that is, a case of linear motion (A), a case of bending due to the photosensitive material (B), and a case of ion sputtering from a bottom having been etched (C). Therefore, plasma ions exhibiting the bending phenomenon and the sputtering phenomenon attacks the side walls of the metal line layer 210, so that the side walls of the metal line layer 210 are over-etched as to form the shape shown in Fig. 2B. Since the first Ti/ TiN layer 210a has physical properties different from the Al layer, the sputtering of plasma ions mainly tends to occur from a time point when the first Ti/ TiN layer 210a is exposed.

Please replace the paragraph [0025] with the following amended paragraph:

**[0026]** Referring to Fig. 2C, by removing the photosensitive material 220 and allowing the Al layer 210b to react with ozone  $O_3$ , an  $Al_2O_3$  film 230 is grown on the side walls of the Al layer 210b. The  $Al_2O_3$  film 230 is grown to compensate for a thickness of over-etched portions of the Al layer 210b. There was a problem that the Al layer is corroded when the metal line layer is exposed to an atmosphere for a long time. However, by previously growing the  $Al_2O_3$  film 230, corrosion of the Al layer can be originally prevented. It is obvious that the kind of film to be oxidized can be changed depending upon the kind of metal formed.